Hexagonal lattice model of the AA-stacked bilayer graphene

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Abstract

Tight-binding model of the AA-stacked bilayer graphene with screened electron-electron interactions has been studied using the Hybrid Monte Carlo simulations on the original double-layer hexagonal lattice. Instantaneous screened Coulomb potential is taken into account using Hubbard-Stratonovich transformation. G-type antiferromagnetic ordering has been studied and the phase transition with spontaneous generation of the mass gap has been observed. Dependence of the antiferromagnetic condensate on the on-site electron-electron interaction is examined.



Finally we arrive at the following expression:

$$Z = \int \mathcal{D}\varphi \mathcal{D}\overline{\eta} \mathcal{D}\eta \mathcal{D}\overline{\chi} \mathcal{D}\chi e^{-\overline{\eta}M\eta - \overline{\chi}M^{+}\chi - \frac{1}{2\Delta\tau}\varphi^{T}\hat{V}^{-1}\varphi}$$
$$= \int \mathcal{D}\varphi det(M^{+}M)e^{-\frac{1}{2\Delta\tau}\varphi^{T}\hat{V}^{-1}\varphi}$$

Fermionic determinant is positive!

The observable: AFM condensate. Electron density operators:

$$\hat{n}_{iA\uparrow} = \frac{1}{N_{subl.}} \sum_{X \in A} \hat{a}^{+}_{X_{A},i\uparrow} \hat{a}_{X_{A},i\uparrow}$$
$$\hat{n}_{iB\downarrow} = \frac{1}{N_{subl.}} \sum_{X \in B} \hat{a}^{+}_{X_{B},i\downarrow} \hat{a}_{X_{B},i\downarrow}$$
$$\Delta n = \langle \hat{n}_{1A\uparrow} \rangle - \langle \hat{n}_{2A\uparrow} \rangle = \langle \hat{n}_{1B\downarrow} \rangle - \langle \hat{n}_{2B\downarrow} \rangle$$

Monolayer graphene and bilayer graphene

Monolayer graphene is represented by a single sheet of carbon atoms, which form hexagonal lattice. Each carbon atom has 4 valence electrons, 3 of them form σ -bonds and the last remains on π -orbital.



Figure 1: Atomic structure of monolayer graphene. Electrons on π -orbitals are oriented perpendicular to the graphene plane.

Bilayer graphene is represented by two graphene sheets, stacked upon each other.



Near the Dirac points:

$$\epsilon = v_F |\mathbf{k}|,$$

where
$$v_F = \frac{3}{2}ta \approx \frac{1}{315} \Rightarrow$$

- coupling constant $\alpha = \frac{e^2}{v_F} \approx 2.3$, in AA-BLG we have **elec**trodynamics with a strong interaction
- magnetic and retardation effects can be neglected, **only** Coulomb interaction may be considered

Interaction potentials: screened Coulomb inside the graphene layer, usual Coulomb between the layers.





In terms of inverse Dirac operator:





Figure 2: *Two common types of bilayer graphene. Energy* spectrum of electrons and transport properties depends heavily on the way of stacking.

We concentrate on the AA-stacked bilayer graphene (AA-BLG).



Figure 3: Atomic structure of the elementary cell of AA-



Figure 6: There are arguments from mean-field theory, that Coulomb interaction in the AA-BLG may open the energy gap and lead to formation of G-type AFM condensate [3]

We start from the Hamiltonian formulation of partition function. Hamiltinian is formulated in terms of electrons and holes:

Lattice formulation

$$\hat{H} = \hat{H}_{tb} + \hat{H}_{stag.} + \hat{H}_{int.}$$

$$\hat{H}_{tb} = -t \sum_{i=1}^{2} \sum_{\langle X_i, Y_i \rangle} (\hat{a}_{X_i}^+ \hat{a}_{Y_i} + \hat{b}_{X_i}^+ \hat{b}_{Y_i}) - t_0 \sum_{X} (\hat{a}_{X_1}^+ \hat{a}_{X_2} + \hat{b}_{X_1}^+ \hat{b}_{X_2}) + h.c.$$

$$\hat{H}_{st.} = \sum_{i=1}^{2} \sum_{X,Y} \pm m \hat{a}_{X_i}^+ \hat{a}_{Y_i} \pm m \hat{b}_{X_i}^+ \hat{b}_{Y_i},$$

where the sign before m in the \hat{H}_{st} are chosen according to the left part of Fig. 6. Electron-electron interaction are

Figure 7: The dependence of the AFM condensate on the on-site interaction potential V_{xx} at fixed temperature. AFM condensate vanishes at the value (8.89 \pm 0.33) eV.

Here we have disagreement with MF result: $\Delta n \approx 0.5$ at $V_{xx} = 8.9 \text{ eV}$ [3].



Figure 8: The dependence of the AFM condensate on temperature, measured on lattices with different temporal sizes. All potentials, except V_{xx} , were rescaled by the factor of $\epsilon = 3.0$: $V_{XY}^{ij} \rightarrow V_{XY}^{ij}/3.0$.

Conclusions

BLG $(a_s = 1.42 \text{ A}, l_s = 3.3 \text{ A}).$

Tight-binding Hamiltonian for electrons in the AA-BLG may be written as follows:

$$\hat{H}_{tb} = -t \sum_{i=1}^{2} \sum_{\langle X_i, Y_i \rangle} \sum_{\sigma=\uparrow,\downarrow} \hat{a}^+_{X_i\sigma} \hat{a}_{Y_i\sigma} - t_0 \sum_{X} \sum_{\sigma=\uparrow,\downarrow} \hat{a}^+_{X_1\sigma} \hat{a}_{X_2\sigma} + h.c.,$$

where $\hat{a}_{X_i\sigma}^+$ and $\hat{a}_{X_i\sigma}$ are creation and annihilation operators for the electron with spin σ at the site X on the layer i respectively, t = 2.57 eV represents nearest-neighbour hopping inside one layer and $t_0 = 0.36 \text{eV}$ — between layers (values of hoppings are taken from [1]).

Energy spectrum of such system has the following form:

added by



where $\hat{q}_{X_i} = \hat{a}_{X_i}^+ \hat{a}_{X_i} - \hat{b}_{X_i}^+ \hat{b}_{X_i}$ and V_{XY}^{ij} is the matrix of potentials.

Exponentials in partition function are splitted as follows:

 $Z = Tr\left(e^{-\beta\hat{H}}\right) = Tr\left(e^{-\Delta\tau(\hat{H}_{tb} + \hat{H}_{stag.} + \hat{H}_{int.})}\right)^{N_t} =$ $= Tr\left(e^{-\Delta\tau(\hat{H}_{tb}+\hat{H}_{st.})}e^{-\Delta\tau\hat{H}_{int.}}e^{-\Delta\tau(\hat{H}_{tb}+\hat{H}_{st.})}\dots\right) + O(\Delta\tau^2)$

Important feature: there are now $2N_t$ time layers due to such splitting, only even time layers are physical. To deal with $e^{-\Delta \tau H_{int.}}$ we perform Hubbard-Stratonovich transformation [4]:

$e^{-\frac{\Delta\tau}{2}\sum_{X,Y}\hat{q}_X V_{XY}\hat{q}_Y} = \int \mathcal{D}\varphi e^{-\frac{1}{2\Delta\tau}\sum_{X,Y}\varphi_X V_{XY}^{-1}\varphi_Y - i\sum_X\varphi_X\hat{q}_X}$

- Original hexagonal lattice model for AA-bilayer graphene with long-range Coulumb interaction was studied.
- Formation of the AFM condensate was observed and its dependence on the on-site electron-electron interaction was examined.

References

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